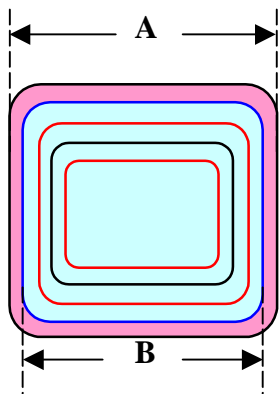


<div>Features :</div> <div><ul style="list-style-type: none">* Extremely low forward volts* Guard ring protection* Low reverse leakage current</div> <div></div>	Chip size(A):	0.814 * 0.814 mm ²		
	Bond Pad size(B)) :	0.686 * 0.686 mm ²		
	Thickness :	300μm ± 20μm		
	Metalization :	Anode Ti/Ni/Ag		
	Metalization :	Cathode Ti/Ni/Ag		
Electrical Characteristics	Sym.	Spec. Limit	Unit	
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C	VF max	0.44	Volt	
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C	VR min.	23	Volt.	
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	25	Amp	
Storage Temperature	TSTG	-65 to +125	°C	

HsinChu Headquarter

5F, No. 11, Park Avenue II,
Science-Based Industrial Park,
HsinChu City, Taiwan
TEL: +886-3-567 9979
FAX: +886-3-567 9909

Sales & Marketing

11F, No. 306-3, SEC. 1, Ta Tung Road,
Hsichih, Taipei Hsien 221, Taiwan
TEL: +886-2-8692 1591
FAX: +886-2-8692 1596